Arkka Bhattacharyya

List of Publications by Year
in descending order

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24	692	566801 15	642321 23
papers	citations	h-index	g-index

24	24	24	413
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Electronic and ionic conductivity in Î²-Ga2O3 single crystals. Journal of Applied Physics, 2022, 131, .	1.1	5
2	4.4 kV Î²-Ga₂O₃ MESFETs with power figure of merit exceeding 100 MW cm^{â^'2}. Applied Physics Express, 2022, 15, 061001.	1.1	40
3	On the terahertz response of metal-gratings on anisotropic dielectric substrates and its prospective application for anisotropic refractive index characterization. Journal of Applied Physics, 2022, 131, .	1.1	3
4	Lateral Gallium Oxide Field Effect Transistors with High Figure of Merit. , 2022, , .		0
5	Oxygen annealing induced changes in defects within Î²-Ga₂O₃ epitaxial films measured using photoluminescence. Journal Physics D: Applied Physics, 2021, 54, 174004.	1.3	11
6	N-type doping of low-pressure chemical vapor deposition grown Î²-Ga2O3 thin films using solid-source germanium. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	14
7	130ÂmAÂmm^{â^'1} Î²-Ga₂O₃ metal semiconductor field effect transistor with low-temperature metalorganic vapor phase epitaxy-regrown ohmic contacts. Applied Physics Express, 2021, 14, 076502.	1.1	39
8	In Situ Dielectric Al₂O₃/Î²â€Ga₂O₃ Interfaces Grown Using Metalâ€“Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	2.6	17
9	High-k Oxide Field-Plated Vertical (001) Î²-Ga₂O₃Schottky Barrier Diode With Baligaâ€™s Figure of Merit Over 1 GW/cm². IEEE Electron Device Letters, 2021, 42, 1140-1143.	2.2	86
10	Ga₂O₃-on-SiC Composite Wafer for Thermal Management of Ultrawide Bandgap Electronics. ACS Applied Materials & Interfaces, 2021, 13, 40817-40829.	4.0	49
11	Spallingâ€Induced Liftoff and Transfer of Electronic Films Using a van der Waals Release Layer. Small, 2021, 17, e2102668.	5.2	4
12	Multi-kV Class Î²-Gaâ„Oâ„ MESFETs With a Lateral Figure of Merit Up to 355 MW/cmÂ². IEEE Electron Device Letters, 2021, 42, 1272-1275.	2.2	50
13	Growth and characterization of metalorganic vapor-phase epitaxy-grown Î²-(Al _x) Tj ETQq1 1 0.784314 rgBT /Overlock 1 channels. Applied Physics Express, 2021, 14, 025501.	1.1	40
14	Low temperature homoepitaxy of (010) Î² -Ga2O3 by metalorganic vapor phase epitaxy: Expanding the growth window. Applied Physics Letters, 2020, 117, .	1.5	56
15	Compensation in (2Â¯01) homoepitaxial Î²-Ga2O3 thin films grown by metalorganic vapor-phase epitaxy. Journal of Applied Physics, 2020, 128, .	1.1	13
16	Defect states and their electric field-enhanced electron thermal emission in heavily Zr-doped Î² -Ga2O3 crystals. Applied Physics Letters, 2020, 117, .	1.5	13
17	Design of a Î²-Ga₂O₃ Schottky Barrier Diode With p-Type III-Nitride Guard Ring for Enhanced Breakdown. IEEE Transactions on Electron Devices, 2020, 67, 4842-4848.	1.6	21
18	Delta-doped Î² -Ga2O3 films with narrow FWHM grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2020, 117, .	1.5	17

#	Article	IF	Citations
19	Synthesis and Characterization of Largeâ€Area Nanometerâ€Thin Î²â€Ga₂O₃ Films from Oxide Printing of Liquid Metal Gallium. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1901007.	0.8	16
20	Delta-doped Î²-Ga₂O₃ thin films and Î²-(Al_{0.26}Ga_{0.74})₂O₃/Î²-Ga₂O₃ heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2020, 13, 045501.	1.3	38
21	Schottky Barrier Height Engineering inÎ²-Ga₂O₃Using SiO₂Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	1.2	32
22	Degenerate doping in Î²-Ga₂O₃ single crystals through Hf-doping. Semiconductor Science and Technology, 2020, 35, 04LT01.	1.0	43
23	Si-doped Î²-(Al_{0.26}Ga_{0.74})₂O₃ thin films and heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2019, 12, 111004.	1.1	47
24	Electrical and optical properties of Zr doped Î²-Ga₂O₃ single crystals. Applied Physics Express, 2019, 12, 085502.	1.1	38